



SI4892DY-T1-GE3 Information



For Reference Only

Part Number SI4892DY-T1-GE3
Manufacturer Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 30V 8.8A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SI4892DY-T1-GE3 Specifications

Manufacturer Part Number SI4892DY-TI-GE3 Manufacturer Vishay Siliconix Category Discrete Semiconductor Products		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package 8-SOIC (0.154", 3.90mm Width) Series TrenchFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 8.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 800mV @ 250μA (Min) Gate Charge (Qg) (Max) @ Vgs 10.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.6W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Manufacturer Part Number	SI4892DY-T1-GE3
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SeriesTrenchFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C8.8A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id800mV @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs10.5nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.6W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 12.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)		Transistors - FETs, MOSFETs - Single
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Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 8.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 10.6W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Series	TrenchFET?
Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C8.8A (Ta)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id800mV @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs10.5nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.6W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 12.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C B. 8.8A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 800mV @ 250μA (Min) Gate Charge (Qg) (Max) @ Vgs 10.5nC @ 5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) #20V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id800mV @ 250μA (Min)Gate Charge (Qg) (Max) @ Vgs10.5nC @ 5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET Feature-Power Dissipation (Max)1.6W (Ta)Rds On (Max) @ Id, Vgs12 mOhm @ 12.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	Drain to Source Voltage (Vdss)	30V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package Package / Case 8-SOIC (0.154", 3.90mm Width)	Current - Continuous Drain (Id) @ 25°C	8.8A (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 1.6W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Vgs(th) (Max) @ Id	800mV @ 250μA (Min)
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FET Feature - Power Dissipation (Max) 1.6W (Ta) Rds On (Max) @ Id, Vgs 12 mOhm @ 12.4A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Input Capacitance (Ciss) (Max) @ Vds	-
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Rds On (Max) @ Id, Vgs12 mOhm @ 12.4A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device Package8-SOPackage / Case8-SOIC (0.154", 3.90mm Width)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Power Dissipation (Max)	1.6W (Ta)
Mounting Type Surface Mount Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Rds On (Max) @ Id, Vgs	12 mOhm @ 12.4A, 10V
Supplier Device Package 8-SO Package / Case 8-SOIC (0.154", 3.90mm Width)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case 8-SOIC (0.154", 3.90mm Width)	Mounting Type	Surface Mount
	Supplier Device Package	8-SO
Report errors?	Package / Case	8-SOIC (0.154", 3.90mm Width)
		Report errors?

SI4892DY-T1-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SI4892DY-T1-GE3 Payment Methods









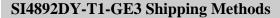
























If you have any question about SI4892DY-T1-GE3, please do not hesitate to contact us!

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